3D Technology for Intelligent Trackers Ronald Lipton, Fermilab WIT 2010

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Oxide bonded 100 micron thick sensors on FPIX (BTeV) wafer

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Future Detectors

- The next generation of detectors will face unprecedented challenges
- ILC Vertex Detector
 - Superb impact parameter resolution ($5\mu m \oplus 10\mu m/(p \sin 3/2\theta)$)
 - Transparency (~0.1% X0 per layer)
- Muon Collider
 - 1-3 TeV muon collider on FNAL site
 - Many accelerator issues
 - Substantial detector and radiation backgrounds
- CLIC
 - ILC + ns time resolution
- SLHC
 - 200-400 int/25 ns crossing
- X-Ray Imaging
 - Variety of challenges timing





It is crucial that we capitalize on the impressive innovations coming from the electronics industry to provide tools for the next generation



- Industry is moving toward 3D to improve circuit performance.
 - Reduce R, L, C for higher speed
 - Reduce chip I/O pads
 - Provide increased functionality
 - Reduce interconnect power and crosstalk
- This is a major direction for the semiconductor industry.

IBM/Cornell/UCSB Study vision of 22 nm 10Tflop 3D chip (2018)

Memory Plane

Logic Plan

3D Ingredients

- Suite of technologies based on:
- 1) Bonding between layers
 - Copper/copper
 - Oxide to oxide fusion.
 - Copper/tin bonding
 - Polymer/adhesive bonding
- 2) Wafer thinning
 - Grinding, lapping, etching, CMP
- 3) Through wafer via formation and metalization
 - With isolation
 - Without isolation (SOI)
- 4) High precision alignment



Unperceivable Bond Interface

imager (Lincoln Labs)



8 micron pitch, 50 micron thick oxide bonded

Moto

Pixel

Photodiodo ti

(Tier 1)



DBI Movie



DBI Studies

- Studied DBI using MIT-LL sensors and BTeV FPIX
- Good connectivity, but some bond voids
- Verified performance
 - X-ray source tests
 - Radiation tests to 10 Mrad
 - Beam tests









3D Tiled Arrays

- These 3D technologies provide the ability to fabricate large area 4-side buttable arrays
- DBI can bond chips with 10 micron spacing
- Topside thinning provides access to interconnects over the full chip area
 - No dead area on edges for interconnects
 - Low impedance connection to ground and power planes
 - Good shielding
- Separation of analog and digital circuit layers

We hope to demonstrate this with the VIPIC and VIP chips in the Tezzaron/Ziptronix run





(Deptuch)

- At SLHC the standard L1 triggers for CMS will saturate
- It is generally agreed that some sort of momentum-based track trigger will be needed to accommodate L~10³⁵
- Such a trigger would need to gather information from 10⁸ pixels in 200m² of silicon at 40 MHz
- Power and bandwidth to send all of the data off-detector is prohibitive
 - Local filtering will be necessary
 - Smart pixels needed to locally correlate hit Pt information
- There are several schemes being studied
 - Correlation of bits between two closely spaced layers
 - Use of cluster width to estimate local curvature
- We are studying the use of 3D for the first option



Data flow:

• Hit information flows from top to bottom tier

•Bottom (master) tier looks for local correlations, filters clusters, and sends data off-module

- Stubs are sent off the rod to a processor which forms local tracks (tracklets) and tracks.
- Tracklets are used to seed full tracks

This technique ensures that all information can be localized into sectors whose size depends on the Pt cutoff

Top to Bottom Data Transfer

- Options:
 - Digital transfer through an interposer
 - Digital transfer at edge
 - Digital transfer through PCB (conventional)
 - Analog transfer through interposer
- 3D allows direct vertical interconnection – allowing for local correlations to be formed, minimizing power and complexity of the logic, allowing fully integrated module design



Model explored in 3D R&D program

Horizontal solutions



Models explored in Pt module R&D program

Data transfer options

- Digital transfer at edge or through interposer
 - Chips must encode/decode hit addresses (power?)
 - Each cluster must be routed at high speed through interposer/PC/interconnect
 - Noise injection into sensor many 100 MHz busses-> current mode transmission or balanced differential signals.
 - Neighbor chip connections will be needed in phi and z
 - Does data need to be buffered? Where?
- Analog transfer from top sensor
 - Possible in 3D design
 - Requires longer (~1 cm) z strips in top tier (limit interposer vias)
 - Allows for *local* processing of correlations (no address decoding)
 - More front-end power due to more capacitive top->bottom connections
 - Single layer may simplify cooling
 - Allows design with only one tier of chips (\$£¢¥)

Z Resolution

- Any trigger based on multiple track objects will benefit from additional z resolution to limit candidate primary vertices
- Z resolution is most relevant for correlations between widely separated doublet hits (stubs are too close)
 - 3D design assumes ~1 cm strips on top and ~1 mm on bottom
 - Top strip (logical) length sets the interposer density in 3D design
- We assume ~1-2 mm z pitch is possible for both conventional and 3D designs. Smaller pitch is possible, but assembly is more complex, technology challenging, and power may be a problem.
- What will be needed for trigger rates? Rate for many triggers is likely to be linear in z resolution.

Demonstration Chip

- Fermilab is sponsoring a two-tier 3D multiproject run with Tezzaron
- Tezzaron (Naperville) has developed a 3D process utilizing CMOS wafers from a commercial IC foundry with cu-cu bonding and "standard" thinning and lith.
- Wafers with "vias first" are made as a process option at Chartered Semiconductor in Singapore.
- Wafers are bonded, thinned and topside processed in Singapore by Tezzaron
 - Bond pads
 - Bump bond pads
- Commercial (10⁶ 8" wafers), well characterized 0.13 micron process
- Chip is intended to demonstrate 3D module interconnect





Tezzaron MPW frame – each circuit contains right and left tiers after bonding

- VIP2b Two –tier implementation of ILC VIP chip
- VIPIC Vertically Integrated Photon Imaging Chip time stamping chip for x-ray imaging
- VICTR 3D chip for sLHC CMS trigger

Status – Continuing struggles with DRC and data validation issues.
'Any day now' for 6 months.



VICTR- Vertically Integrated CMS TRigger Chip

Chartered FEI4 design contributed by ATLAS



Phi strip inputs Тор CMOS(1) Test test in Test 64 bits circuit circuit \rightarrow (2) Ld/clk Hit in $\not \rightarrow$ (2) Ld/clk Т Top OR out LVDS (2) 1 bit And С And LVDS(8) В R В 80 pixels, 8b/pix В on each of 4 output lines Data: TCBBBBBX LVDS(2) Bottom 64 ORs of 5 ORs each Bottom Ч٢ Ч ЧН 1 bit OR out test in CMOS(1) \rightarrow 64 bits (2) Ld/clk Z strip input

Simple chip digital design

- top/bottom coincidence
 - 5x1 mm bottom with 5mm top
- serial readout
- Fast or output

Top Tier – bump bond pad array Bottom tier – DBI bond array

VICTR Top Metal



3D Sensor Integration

Handle Wafer

Tezzaron Wafer after bonding **Bulk Silicon** cu 3D connection **Bulk Silicon Ziptronix Wafers** Thin to top pad side **Bulk Silicon** TSVs Send to Ziptronix **Bulk Silicon** Oxide bond to sor interconnect side handle wafer at Ziptronix Handle Wafer Sensor Wafer

Thin to sensor side TSV at Tezzaron or Ziptronix Grind and etch to TSV, metalize

Dice

DBI Bond

to sensor wafer

3D Fabrication of Stacked Layers



Readout IC wafer with TSV from foundry



Oxide bond diced ROIC to sensor Wafer.



Contact lithography provides Access to topside pads for vertical data path



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Test stack



Module Design

- Modules would be nxm arrays of chips DBI bonded to sensor. This can be done because both top and bottom IC pads are accessible.
 - Chips are bump bonded to interposer
 - Top sensor bump bonded to interposer
- Interposer
 - Transmits top sensor analog signals to ROICs
 - Provides interconnect and power to ROICS
 - Provides readout bus interconnect
 - Flex output to optical components
- We are asking a lot of the interposer major R&D area



Local Trigger Logic



- 3D design allows for local trigger logic simple example
- Each strip looks at ~ 4 neighbors
 - Kill all hits if cluster is too large
 - Central strip outputs hit information to internal logic
 - Interpolation to ½ strip
 - Can output in Pt bins if required
- External settings for dead or noisy strips, shift of information in phi, pt threshold
- Neighbor chip sends cluster information for last short strips
- Pipelined in ~4 steps to allow wide cluster killing, neighbor transfers, cluster formation

Interconnect and rates

- Assume 2 cm x 2 cm chip
 - 200 x 2 analog vias (for 100µm pitch, 1 cm long strips)
 - Data bus ~ 22 bits, control~8 bits, neighbor ~ 20 bits, power/gnd ~ 20 = 70 interconnects
 - Assume 500/chip Interposer bump bond spacing ~ 800 microns
- Rate/module
 - Rough estimate at about
 35 cm based on Fast MC
 - Full MC 3x higher rate
 - Add event readout (few %)
 - 2.25 stubs/xing/module
 - ~2 GHz bit rate/module
- Very large uncertainties (x5?)
- Needs continued detailed MC
- Needs (has?) data



In-Module Data Transfer

- High rate bus in close proximity to sensors
- All designs but analog transfer require transfer of some digital data at full hit rate within the module
 - Proper electrical shielding will be crucial
- Transfer cluster information across chips.
- In 3D design both horizontal and vertical transfers must be integrated
 - Extra PC board or flex layers
 - Integration of horizontal bus on interposer
 - Other technical solutions (twisted wire ...)
 - Bump bonds include both analog and digital transfer
 - Guess about 125 bumps/cm² mostly analog





Data Readout (M. Johnson)

- Micropipelined data transfer between chips
- Tri state possible?
- Event data (5%) appended to trigger data
- Can be configured to use 1/2 , 1 or 2 GBT/module

| Pipeline Step | Operation |
|---------------|--|
| One | Form phi clusters for both sensors |
| Тwo | Send boundary phi clusters across chip boundary to the right |
| Three | Send z data across long z and chip boundaries |
| Four | Form stubs for trigger |
| Five | Send trigger and event data to top of chip column |
| Six | Send trigger and event data across top of chip to fiber driver |
| Seven | Send data over fiber line to off detector system |



~20 MHz x 22 bits/column



Power

- Analog most well defined P ~ C²_{load}
- Digital
 - Base chip power (14 mW/chip) $P = k \times freq \times C_{int}V^2$
 - Chip hit processing power (assume 180 pJ/hit) ???
 - Data transmission from master to slave (0.5 pf)
 - Stub transmission to optical interconnect 12 cm x .8pf/cm
 - Optical link power (nlinks/rod)
 - Link picojoule/bit numbers range from 50 625
- Survey of RO Chip estimates single layer only not really apples/apples
 - ~ 80μ W/pixel \rightarrow 0.032 W/cm² (GH)
 - ~ 0.026 W/cm² (MM+RH)
 - ~ 0.034 W/cm² (RL one analog tier 3D)
 - CMS pixel chip 0.194 W/cm² ~ 7x more
- Not including 1/(.75-.8) penalty for DC-DC conversion

Mass

- DC-DC converter and GBT not included
 - Copper 2x D0 HDI density, low mass interposer
- How to minimize mass (in 3D design)
 - Minimize copper
 - Low mass interposer
 - Local bypass of power lines (?)
 - Foam spacer
 - "swiss cheese" silicon



Radiation Length



Module Fabrication

- Use 3D analog module as example
 - Assemble interposer with electronics
 - Bed of nails test?
 - Sacrificial test connector?
 - Test components
 - Test ROIC die on production wafer
 - Test sensors
 - DBI bond die to sensor (industry)
 - Glue sensors to bottom CF, Kapton (HV connection)
 - Bump bond interposer to bottom sensor
 - Test bottom assembly
 - Bump bond sensor/interposer to top sensor
 - Test full module







Parts for Vertical Module

SOI or MAPS Sol 1st generation ANALOG /DIGITAL **300**µm pixels g-rings

or

DETECTOR

less

BOX

& det bias

DET_BIAS

Twisted Wire Interconnector Twisted wire interposer True Z-Axis Interconnection Solderless & Reworkable Simplifies PCB Layout

Replaces Traditional Connector Systems

Silicon Interposer





Vertically Interconnected Module conceptual design



Application to Muon Collider

Muon Collider VTX

- Muon collider has very high occupancy near the vertex
- S. Geer suggested a stacked layer design to reduce occupancy based on inter-layer correlations for the muon collider in 1998
- This technology looks very much like what we are developing for the CMS upgrade

1999 μCol Track correlation module





2009 Track trigger module for CMS Phase II Based on 3D electronics



Conclusions

- Track trigger modules seems to be an ideal application for 3D/SOI
- Initial studies of bandwidth, rejection, power look promising
- Need to understand cost and yield issues
- Studying the design parameters:
 - Stub rejection correlation algorithms
 - Algorithm and connectivity how much is hard-wired?
 - Pt threshold
 - Power consumption IC design modeling
 - Power consumption optical link power
 - Power consumption data bandwidth
 - Z segmentation
- We are investigating the concept in the FNAL 3D multiproject run

Building a Trigger module with 3D



Readout IC wafer with TSV from foundry



Oxide bond diced ROIC to sensor Wafer.



Thin to expose TSV



Contact lithography provides Access to topside pads for vertical data path



VICTR Logic and Floorplan







